

CLAIM AMENDMENTS

1. (Currently Amended) A semiconductor device, comprising:  
a ~~first~~ conductive layer;  
a first contact comprising a ball on said first conductive layer;  
a ~~second conductive layer~~ bonding pad spaced apart from said ~~first~~ conductive layer;  
a second contact on said ~~second conductive layer~~ first bonding pad; and  
a bonding wire electrically connecting said first contact ~~and to~~ said second contact,  
wherein said second contact includes at least two layers of said bonding wire, lying directly  
on each other, so that said bonding wire including includes at least one reverse bend, and one  
of the layers is in contact with said first bonding pad.

2 and 3 (Previously Cancelled)

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4. (Currently Amended) The semiconductor device according to claim 1, wherein  
said ~~first~~ conductive layer includes an inner lead, ~~and said second conductive layer includes a~~  
~~bonding pad.~~

5. (Currently Amended) The semiconductor device according to claim 1, comprising  
a base;  
a semiconductor element on said base with a die pad interposed between said  
semiconductor element and said base;  
a sealing resin sealing said semiconductor element; and  
an external terminal on a rear surface of said base, wherein  
said ~~first~~ conductive layer includes a land on said base, and  
said ~~second conductive layer includes a~~ first bonding pad is on said  
semiconductor element.

6. (Currently Amended) The semiconductor device according to claim 1,  
comprising:  
a base;  
first and second semiconductor elements mounted on said base with a die pad  
interposed between said base and said first and second semiconductor elements;  
a sealing resin sealing said first and second semiconductor elements; and  
an external terminal on a rear surface of said base, wherein

said ~~first~~ conductive layer includes a ~~first~~ second bonding pad on said first semiconductor element, and

said ~~second conductive layer includes a second~~ first bonding pad is on said second semiconductor element.

7. (Currently Amended) A method of manufacturing a semiconductor device, comprising, sequentially:

joining a ball formed at a tip end of a bonding wire to a ~~first~~ conductive layer as a first contact;

joining a first part of said bonding wire directly to a ~~second conductive layer~~ bonding pad;

mechanically deforming a second part of said bonding wire, while said first part of said bonding wire is joined to ~~the second conductive layer~~ said bonding pad, so that said bonding wire is folded onto said first part of said bonding wire, directly opposite said ~~second conductive layer~~ bonding pad; and

joining said second part of said bonding wire to said first part of said bonding wire on said ~~second conductive layer~~ bonding pad.

8 and 9 (Previously Cancelled)

10. (Currently Amended) The method of manufacturing a semiconductor device according to claim 7, wherein

said bonding wire is held by a bonding tool; and

mechanically deforming said bonding wire includes mechanically deforming said bonding wire on said ~~second conductive layer~~ bonding pad by moving said bonding tool with said bonding wire joined to said ~~second conductive layer~~ bonding pad.